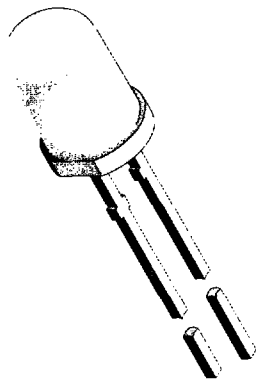
GaAs Infrared Emitting Diodes in ø 5 mm (T–1¾) Package

Description

TSUS520. series are infrared emitting diodes in standard GaAs on GaAs technology, molded in a clear, blue–grey tinted plastic package. The devices are spectrally matched to silicon photodiodes and phototransistors.



Features

- Low cost emitter
- Low forward voltage
- High radiant power and radiant intensity
- Suitable for DC and high pulse current operation
- Standard T–1¾ (ø 5 mm) package
- Angle of half intensity $\varphi = \pm 15°$
- Peak wavelength $\lambda_p = 950$ nm
- High reliability
- Good spectral matching to Si photodetectors

Applications

Infrared remote control and free air transmission systems with low forward voltage and low cost requirements in combination with PIN photodiodes or phototransistors.

Absolute Maximum Ratings

$T_{amb} = 25°C$

Parameter	Test Conditions	Symbol	Value	Unit
Reverse Voltage		V_R	5	V
Forward Current		I_F	150	mA
Peak Forward Current	$t_p/T=0.5$, $t_p=100$ µs	I_{FM}	300	mA
Surge Forward Current	$t_p=100$ µs	I_{FSM}	2.5	A
Power Dissipation		P_V	210	mW
Junction Temperature		T_j	100	°C
Operating Temperature Range		T_{amb}	–55...+100	°C
Storage Temperature Range		T_{stg}	–55...+100	°C
Soldering Temperature	t ≦ 5sec, 2 mm from case	T_{sd}	260	°C
Thermal Resistance Junction/Ambient		R_{thJA}	375	K/W

Basic Characteristics

T_{amb} = 25°C

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward Voltage	I_F = 100 mA, t_p = 20 ms	V_F		1.3	1.7	V
Temp. Coefficient of V_F	I_F = 100mA	TK_{VF}		-1.3		mV/K
Reverse Current	V_R = 5 V	I_R			100	µA
Junction Capacitance	V_R = 0 V, f = 1 MHz, E = 0	C_j		30		pF
Temp. Coefficient of ϕ_e	I_F = 20 mA	$TK_{\phi e}$		-0.8		%/K
Angle of Half Intensity		φ		±15		deg
Peak Wavelength	I_F = 100 mA	λ_p		950		nm
Spectral Bandwidth	I_F = 100 mA	$\Delta\lambda$		50		nm
Temp. Coefficient of λ_p	I_F = 100 mA	$TK_{\lambda p}$		0.2		nm/K
Rise Time	I_F = 100 mA	t_r		800		ns
	I_F = 1.5 A	t_r		400		ns
Fall Time	I_F = 100 mA	t_f		800		ns
	I_F = 1.5 A	t_f		400		ns

Type Dedicated Characteristics

T_{amb} = 25°C

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward Voltage	I_F=1.5A, t_p=100µs	TSUS5200/5201	V_F		2.2	3.4	V
		TSUS5202	V_F		2.2	2.7	V
Radiant Intensity	I_F=100mA, t_p=20ms	TSUS5200	I_e	10	20		mW/sr
		TSUS5201	I_e	15	25		mW/sr
		TSUS5202	I_e	20	30		mW/sr
Radiant Intensity	I_F=1.5A, t_p=100µs	TSUS5200	I_e	95	180		mW/sr
		TSUS5201	I_e	120	230		mW/sr
		TSUS5202	I_e	170	280		mW/sr
Radiant Power	I_F=100mA, t_p=20ms	TSUS5200	ϕ_e		13		mW
		TSUS5201	ϕ_e		14		mW
		TSUS5202	ϕ_e		15		mW

Typical Characteristics (T_{amb} = 25°C unless otherwise specified)

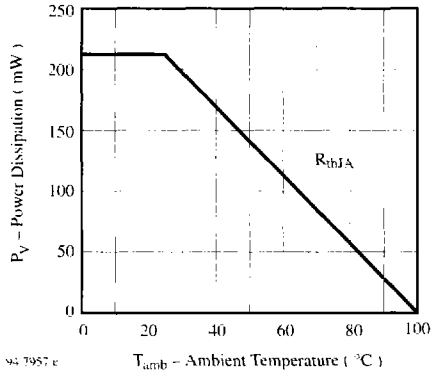


Figure 1. Power Dissipation vs. Ambient Temperature

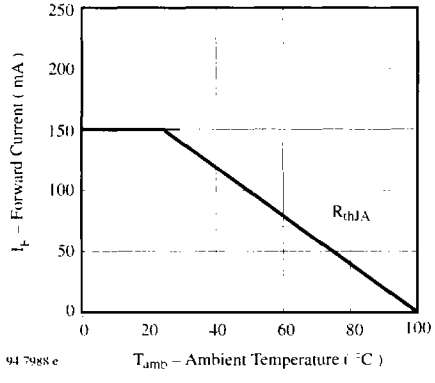


Figure 2. Forward Current vs. Ambient Temperature

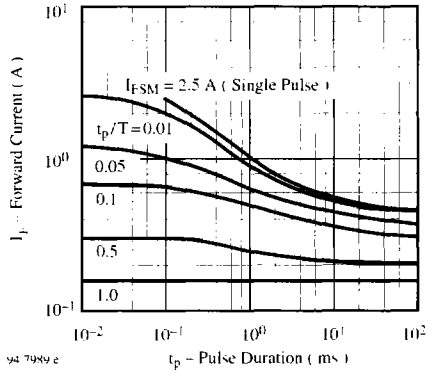


Figure 3. Pulse Forward Current vs. Pulse Duration

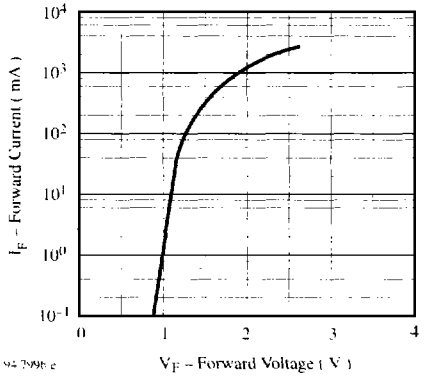


Figure 4. Forward Current vs. Forward Voltage

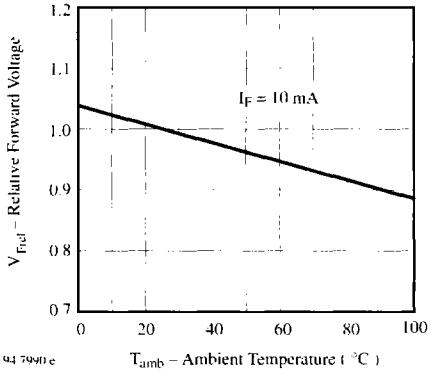


Figure 5. Relative Forward Voltage vs. Ambient Temperature

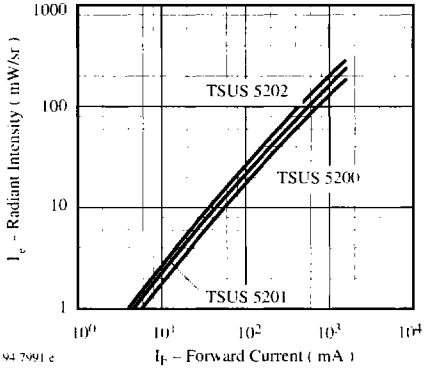


Figure 6. Radiant Intensity vs. Forward Current

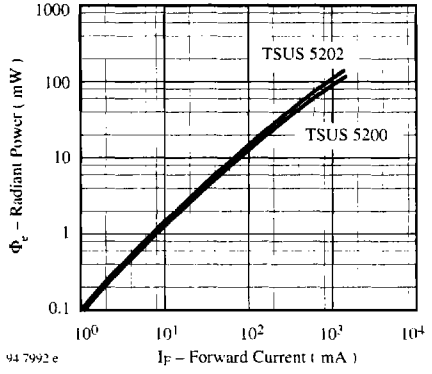


Figure 7. Radiant Power vs. Forward Current

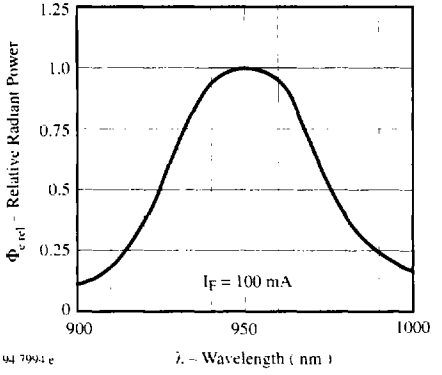


Figure 9. Relative Radiant Power vs. Wavelength

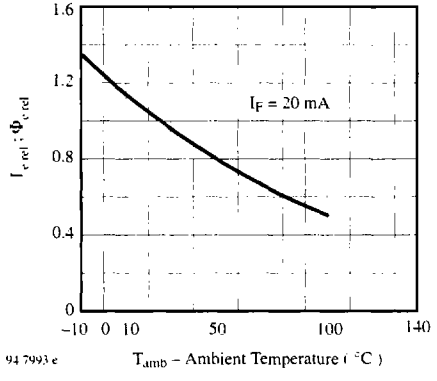


Figure 8. Rel. Radiant Intensity\Power vs. Ambient Temperature

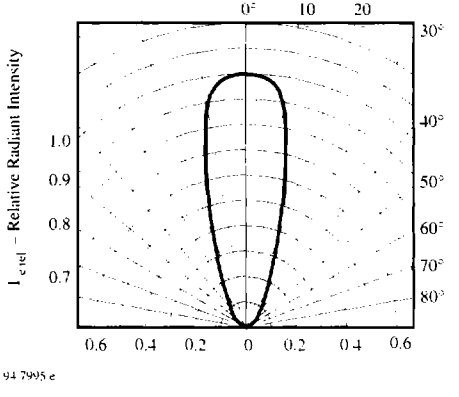


Figure 10. Relative Radiant Intensity vs. Angular Displacement

Dimensions in mm